

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Inventors: A. TAMURA, et al.

Application No.: New Patent Application

Filed: July 24, 2003

For: HETEROJUNCTION FIELD EFFECT TRANSISTOR AND
MANUFACTURING METHOD THEREOF

INFORMATION DISCLOSURE STATEMENT

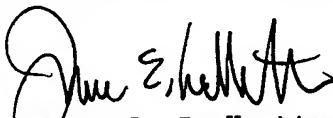
Honorable Commissioner of
Patents and Trademarks
Washington, DC 20231

Sir:

Pursuant to Rules 56 and 99, Applicants hereby call the
attention of the Patent Office to the reference(s) listed on the
attached Form PTO 1449. The J. ABROKWAH, et al. and N. HAYAFUJI, et
al. documents are discussed in the background section of the
application at page 1, line 17 - page 2, line 24.

Applicants present this art so that the Patent Office may, in the first instance, determine any relevancy thereof to the presently claimed invention, see Beckman Instruments, Inc. v. Chemtronics, Inc., 439 F.2d 1369, 1380, 165 USPQ 355, 364 (5th Cir. 1970). Also see Patent Office Rules 104 and 106. Applicants respectfully request that this art be expressly considered during the prosecution of this application and made of record herein and appear among the "References Cited" on any patent to issue herefrom.

Respectfully submitted,



James E. Ledbetter
Registration No. 28,732

Date: July 24, 2003

JEL/apg

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<p>FORM PTO-1449 U.S. Department of Commerce (Rev. 4/92) Patent and Trademark Office</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(Use several sheets if necessary)</p>	ATTY. DOCKET NO.	SERIAL NO.
	L8462.03106	Unassigned
	APPLICANT	A. TAMURA, et al.
FILING DATE	July 24, 2003	GROUP
		Unassigned

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	J. ABROKWAH, et al., "A Manufacturable Complementary GaAs Process", IEEE, 1993, pp. 127-130
	N. HAYAFUJI, et al., "Thermal Stability of AlInAs/GaInAs/InP Heterostructures", American Institute of Physics, February 1995, pp. 863-865

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.